

BRD50P06Q

Rev.A Sep.-2024



DATA SHEET

TO-252 P MOS

P-CHANNEL MOSFET in a TO-252 Plastic Package.

Low $R_{DS(on)}$, low gate charge, low C_{rss}

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-60	V
Drain Current	$I_D(T_C=25)$	-50	A
Drain Current - Pulsed	I_{DM}	-200	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation	$P_D(T_C=25)$	85	W
Single Pulsed Avalanche Energy	E_{AS}	250	mJ
Avalanche Current(L=0.5mH)	I_{AS}	25	A
Junction and Storage Temperature Range	T_j, T_{stg}	-55 to 150	
Thermal resistance, junction - ambient	$t = 10s$	R_{JA}	/ W
	Steady-State		
Thermal resistance, junction - case	Steady-State	R_{JC}	1.5

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=-250\mu A$	-60	-68		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-60V$ $V_{GS}=0V$			-1.0	μA
		$V_{DS}=-48V$ $T_C=150$			-10	
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 0.1	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=-250\mu A$	-1	-1.6	-3	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V$ $I_D=-20A$		30	35	m
	$R_{DS(on)}$	$V_{GS}=-4.5V$ $I_D=-10A$		40	45	m
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=-1A$			-1.2	V
Gate resistance	R_g			10		
Input Capacitance	C_{iss}	$V_{DS}=-25V$ $V_{GS}=0V$ $f=1.0MHz$		3200		pF
Output Capacitance	C_{oss}			800		pF
Reverse Transfer Capacitance	C_{rss}			270		pF
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=-10V,$ $V_{DS}=-30V,$ $I_D=-20A$		45		nC
Total Gate Charge	$Q_{g(4.5V)}$			23		
Gate Source Charge	Q_{gs}			9.3		
Gate Drain Charge	Q_{gd}			10.2		

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=-10V$ $V_{DS}=-30V$ $R_L=1.5$ $R_{GEN}=3$		12		ns
Turn-On Rise Time	t_r			14.5		
Turn-Off Delay Time	$t_{d(off)}$			38		
Turn-Off Fall Time	t_f			15		

/ Electrical Characteristic Curve

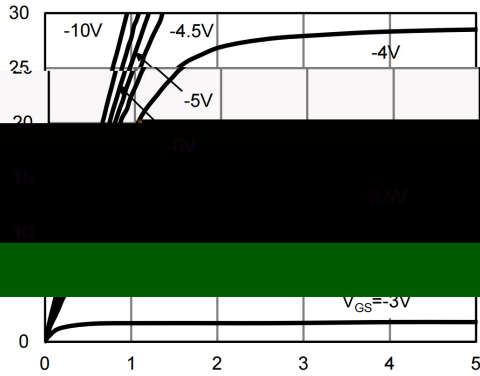


Figure 1: On-Region Characteristics

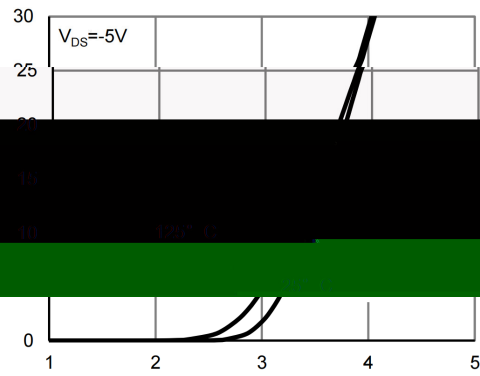


Figure 2: Transfer Characteristics

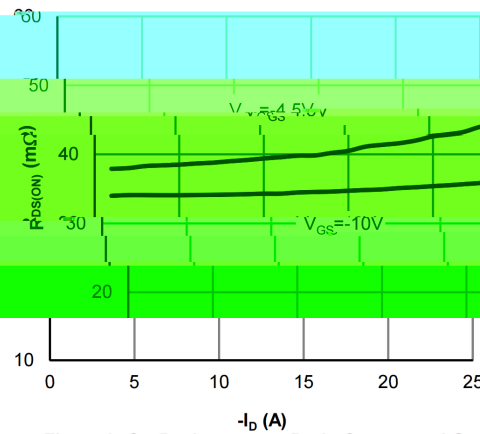


Figure 3: On-resistance vs. Drain Current and Gate-Source Voltage

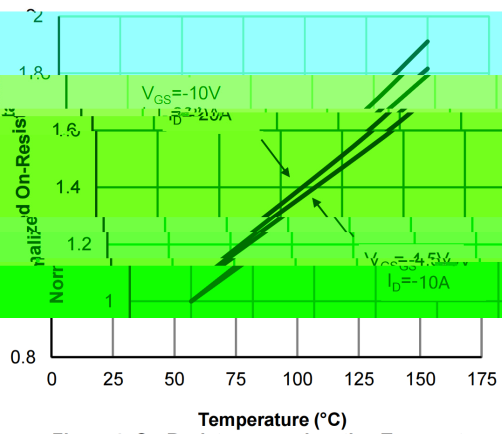


Figure 4: On-resistance vs. Junction Temperature

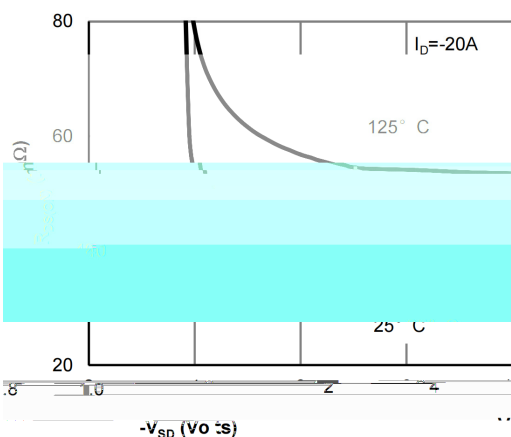


Figure 5: On-resistance vs. Drain-Source Voltage

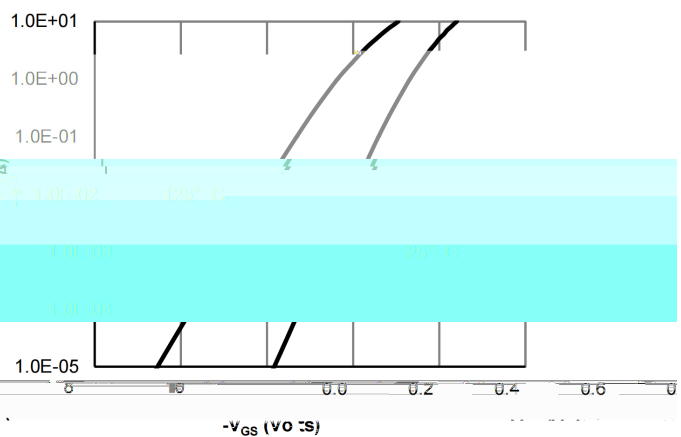
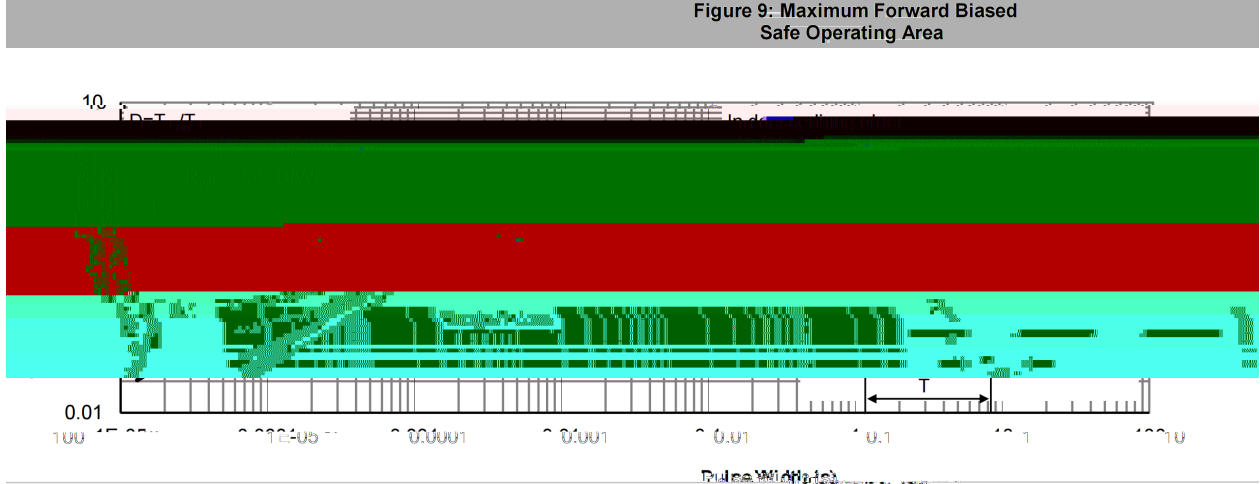
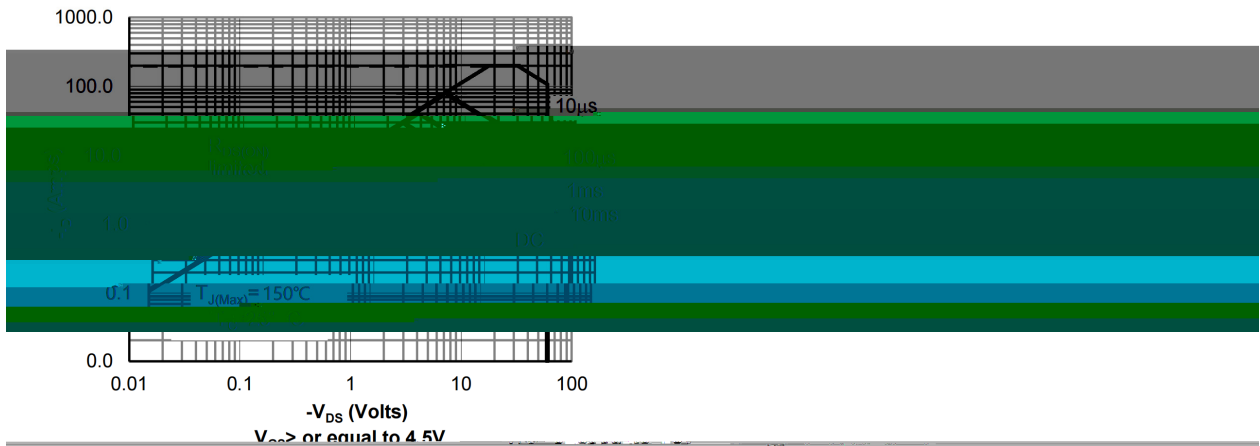
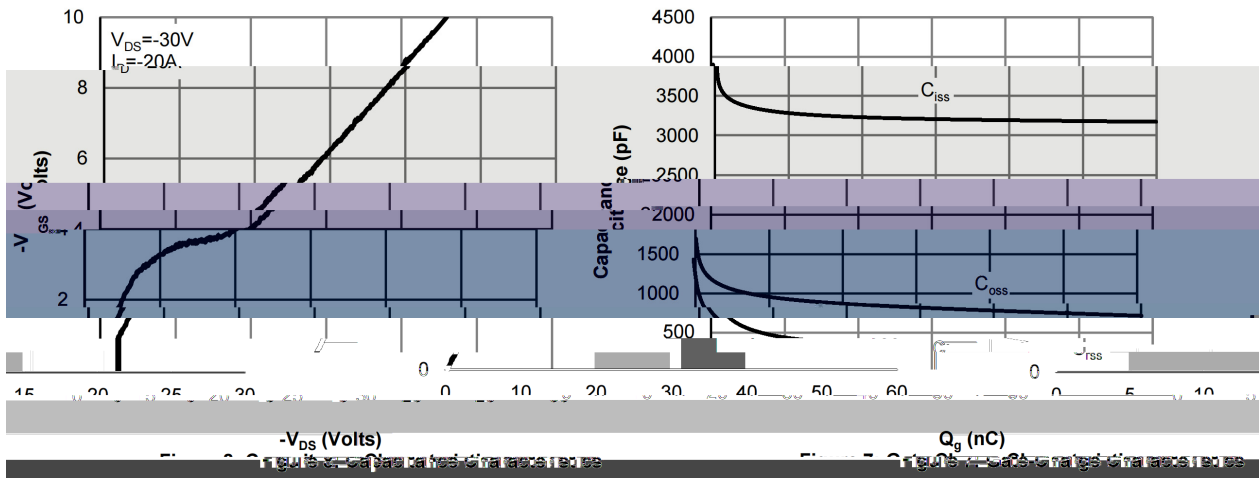
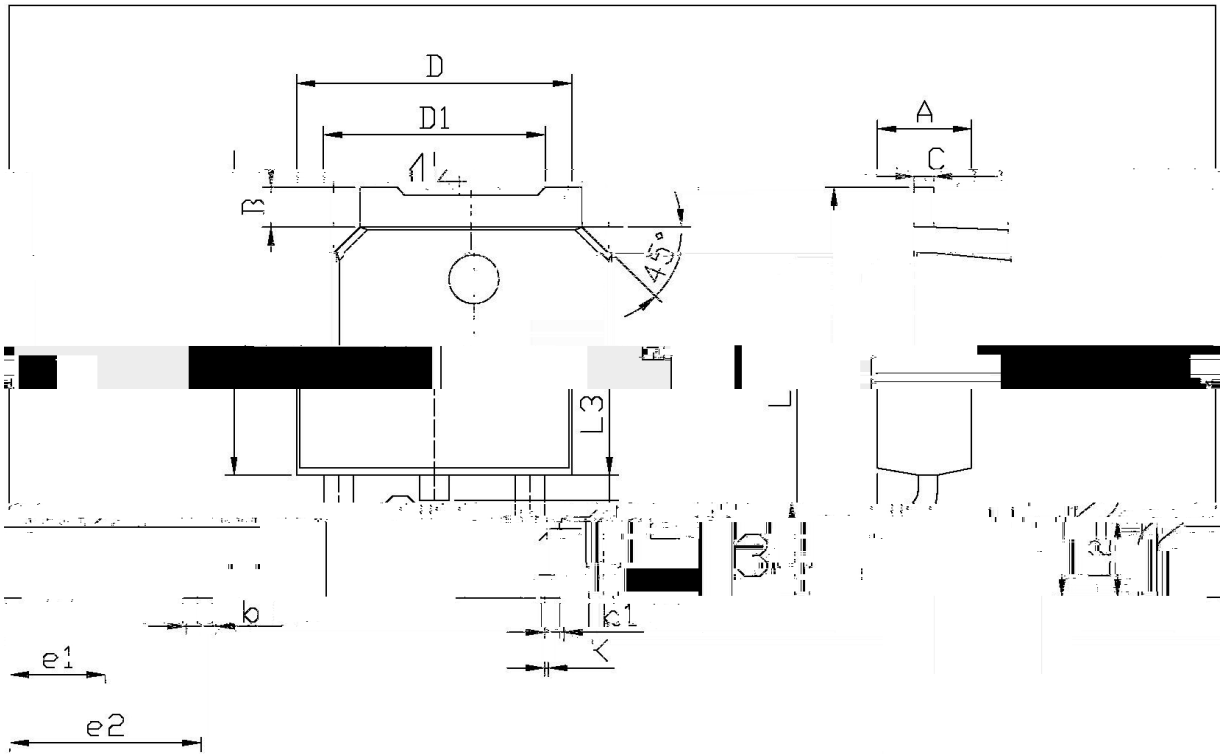


Figure 6: On-resistance vs. Gate-Source Voltage

/ Electrical Characteristic Curve



/ Package Dimensions

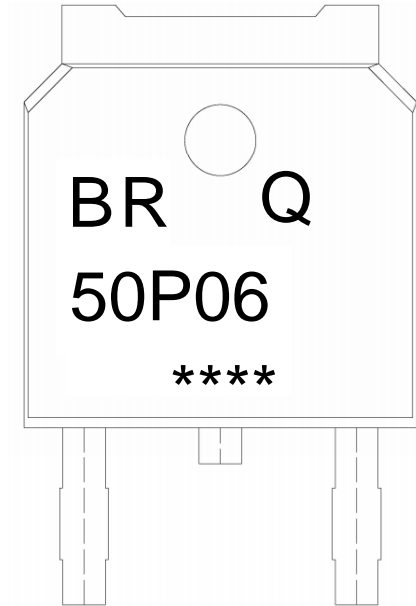


单位: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	2.20	2.70	F	1.25	1.50
B	0.95	1.25	e1	2.24	2.34
b1	0.70	0.90	L1	9.85	10.35
b	0.45	0.55	L3	0.60	0.90
D	6.45	6.75			

TO-252

/ Marking Instructions



BR
Q

Note:

BR: Company Code

Q: Automobile halogen-free product Code

50P06: Product Type Code

****: Lot No. Code, code change with Lot No

() / Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

- 1 150 200 60 120sec; 1.Preheating:150~200 , Time:60~120sec.
- 2 255 5 5 0.5sec; 2.Peak Temp.:255 5 , Duration:5 0.5sec.
- 3 2 10 /sec. 3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260 5 10 1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units				Dimension			(unit mm ³)